

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,718,987 B2
APPLICATION NO. : 10/589915
DATED : May 18, 2010
INVENTOR(S) : Tow Chong Chong et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

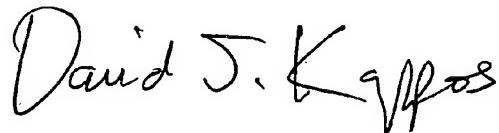
Col 10, claim 13, lines 26–31, delete “structures; and
a second contact wherein said crystallization temperature of said phase change material
of said initial layer and said phase change material of said final layer is in a range from
about 90 degrees Celsius to about 120 degrees Celsius formed over said final layer.”

and insert:

--structures, wherein said crystallization temperature of said phase change material of
said initial layer and said phase change material of said final layer is in a range from
about 90 degrees Celsius to about 120 degrees Celsius; and
a second contact formed over said final layer.--

Signed and Sealed this

Nineteenth Day of October, 2010



David J. Kappos
Director of the United States Patent and Trademark Office